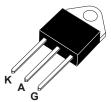


50 A 1200 V SCR in TOP3 insulated





TOP3 Isolated

Features

- Max. repetitive blocking voltage = V_{DRM}, V_{RRM} = 1200 V
- I_{GT} maximum = 80 mA
- ECOPACK2 component (RoHS and HF compliance)
- Complies with UL 1557 standard (File ref : E81734)

Application

- · Solid state relays
- · Welding equipment
- High power motor control
- Heating systems
- Controlled AC/DC bridge

Description

Available in a high power package TOP3-I, the BTW69-1200 is suitable in applications where power handling and power dissipation are critical, such as solid state relays, welding equipment, high power motor control and power converters.

This device offers a superior performance in surge current handling capabilities, allowing usage in industrial environment.

Thanks to its internal ceramic pad, it provide high voltage insulation (2500V_{RMS}), complying with UL standards (file ref: E81734).

Product status link

BTW69-1200

Product summary			
I _{T(RMS)}	50 A		
V _{DRM} /V _{RRM}	1200 V		
I _{GT}	80 mA		



Characteristics

Table 1. Absolute maximum ratings

Symbol	pol Parameters					
I _{T(RMS)}	RMS on-state current (180° conduction angle) $T_c = 75$ °C				Α	
IT _(AV)	Average on-state current $T_c = 75 ^{\circ}\text{C}$ (180° conduction angle)				Α	
l	Non repetitive surge peak on-state current (full cycle, T_j initial = 25 °C, V_R = 0 V) t_p = 8.3 ms t_p = 10 ms				Α	
ITSM					1 A	
I ² t	$t_p = 10 \text{ ms}, T_j = 25^{\circ}\text{C}$				A ² s	
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$ $F = 60 \text{ Hz}$		T _j = 125 °C	50	A/µs	
I _{GM}	Peak gate current $t_p = 20 \mu s$		T _j = 125 °C	8	Α	
P _{G(AV)}	Average gate power dissipation $T_j = 125 ^{\circ}\text{C}$				W	
T _{stg}	Storage junction temperature range				°C	
Tj	Operating junction temperature range			-40 to +125	°C	
V_{GRM}	Maximum peak reverse gate voltage			5	V	
V _{ins}	Insulation RMS voltage, 1 minute				V	

Table 2. Electrical characteristics ($T_j = 25^{\circ}C$, unless otherwise specified)

Symbol	Test conditions		Value	Unit	
la-				8	mA
I _{GT}	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Max	80	- IIIA
V _{GT}			Max	1.3	V
V _{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$	125 °C	Min.	0.2	V
I _H	I_H I_T = 500 mA, gate open		Max.	150	mA
IL	I _G = 1.2 x I _{GT}		Max.	200	mA
dV/dt	V _D = 67 %, V _{DRM} gate open	125 °C	Min.	1000	V/µs
V _{TM}	I _{TM} = 100 A, t _p = 380 μs		Max.	1.9	V
V _{TO}	Threshold on-state voltage	125 °C	Max.	1.0	V
R _D	On-state dynamic resistance	125 °C	Max.	8.5	mΩ
I _{DRM} /I _{RRM}	$V_D = V_{DRM}$, $V_R = V_{RRM}$	25 °C	Max.	10	μA
ייאאטייRRM אויאמיי	AD - ADKW' AK - AKKW	125 °C	ividX.	5	mA

Table 3. Thermal resistance

Symbol	Parameters Parameters Parameters	Value	Unit		
R _{th(j-c)}	Junction to case (D.C)	0.9	°CAM		
R _{th(j-a)}	Junction to ambiant (D.C)	50	°C/W		

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1.1 Characteristics (curves)

Figure 1. Maximum average power dissipation versus average on-state current

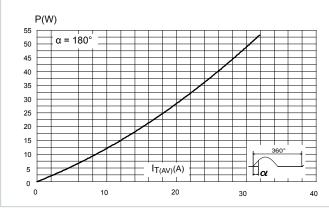


Figure 2. Average on-state current versus case temperature

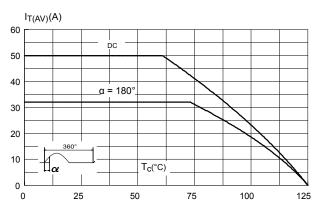


Figure 3. Relative variation of thermal impedance versus pulse duration

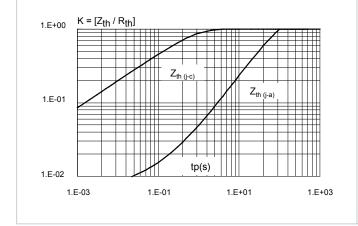


Figure 4. Relative variation of gate trigger current, holding current and latching current versus junction temperature

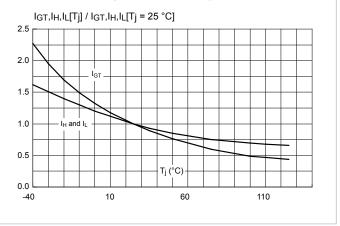


Figure 5. Surge peak on-state current versus number of cycles

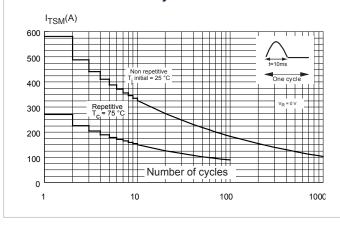
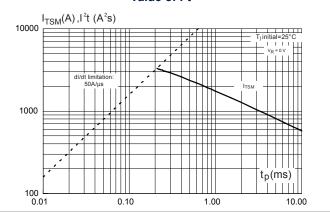


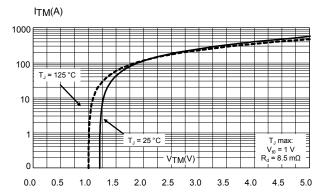
Figure 6. Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p <$ 10 ms, and corresponding value of l^2t



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Figure 7. On-state characteristics (maximum values)



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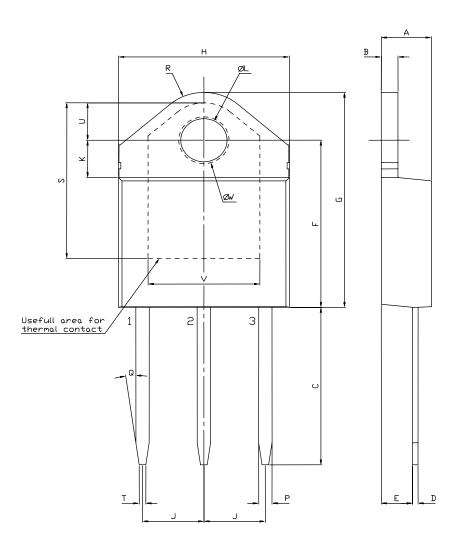
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 TOP3 Ins. package information

- ECOPACK (lead-free plating and halogen free package compliance)
- · Lead-free package leads finishing
- Halogen-free molding compound resin meets UL94 standard level V0
- Recommended torque: 1.05 N·m (max. torque: 1.2 N·m)

Figure 8. Package outline



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Table 4. Mechanical data

				Dimensions		
Ref.		mm			Inches ⁽¹⁾	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.40		4.60	0.1732		0.1811
В	1.45		1.55	0.0571		0.0610
С	14.35		15.60	0.5650		0.6142
D	0.50		0.70	0.0197		0.0276
Е	2.70		2.90	0.1063		0.1142
F	15.80		16.50	0.6220		0.6496
G	20.40		21.10	0.8031		0.8307
Н	15.10		15.50	0.5945		0.6102
J	5.40		5.65	0.2126		0.2224
K	3.40		3.65	0.1339		0.1437
L	4.08		4.17	0.1606		0.1642
Р	1.10		1.30	0.0430		0.0510
R		4.60			0.1811	

^{1.} Inches given for reference only

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3 Ordering information

Figure 9. Ordering information scheme

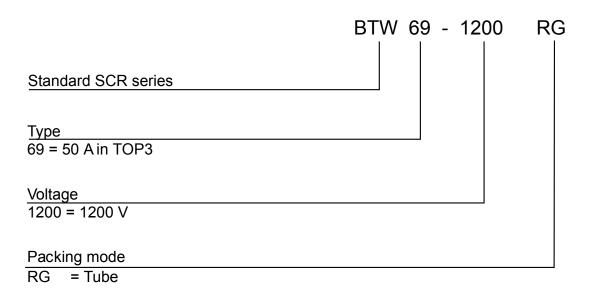


Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
BTW69-1200RG	BTW691200	TOP3 Ins.	4.5 g	30	Tube

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Revision history

Table 6. Document revision history

Date	Revision	Changes
09-Sep-2019	1	Initial release.
26-Jul-2023	2	Updated Table 4. Mechanical data.

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